

Description

The VST03P050 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

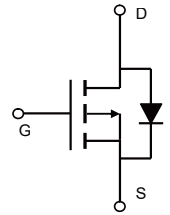
- $V_{DS} = -30V, I_D = -90A$
 $R_{DS(ON)} = 5.7m\Omega$ (typical) @ $V_{GS} = -10V$
 $R_{DS(ON)} = 7.6m\Omega$ (typical) @ $V_{GS} = -4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175°C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



TO-252



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST03P050	VST03P050-T2	TO-252	-	-	-

Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-90	A
Drain Current-Continuous($T_c = 100^\circ\text{C}$)	$I_D(100^\circ\text{C})$	-63	A
Pulsed Drain Current	I_{DM}	-300	A
Maximum Power Dissipation	P_D	90	W
Derating factor		0.6	W/°C
Single pulse avalanche energy ^(Note 5)	E_{AS}	500	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	1.67	°C/W
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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-30		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-1.0	-1.5	-2.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-20A	-	5.7	6.3	mΩ
		V _{GS} =-4.5V, I _D =-20A	-	7.6	8.5	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V, I _D =-20A	-	30	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, F=1.0MHz	-	3700	-	PF
Output Capacitance	C _{oss}		-	880	-	PF
Reverse Transfer Capacitance	C _{rss}		-	20	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V, I _D =-20A V _{GS} =-10V, R _G =1.6Ω	-	10.5	-	nS
Turn-on Rise Time	t _r		-	9	-	nS
Turn-Off Delay Time	t _{d(off)}		-	40	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V, I _D =-20A, V _{GS} =-10V	-	57	-	nC
Gate-Source Charge	Q _{gs}		-	9.8		nC
Gate-Drain Charge	Q _{gd}		-	7.3		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =-20A	-		-1.2	V
Diode Forward Current (Note 2)	I _S		-	-	-90	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =-20A di/dt = 100A/μs ^(Note3)	-		24	nS
Reverse Recovery Charge	Q _{rr}		-		68	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_J=25°C, V_{DD}=-15V, V_G=-10V, L=0.5mH, R_G=25Ω

Typical Electrical and Thermal Characteristics

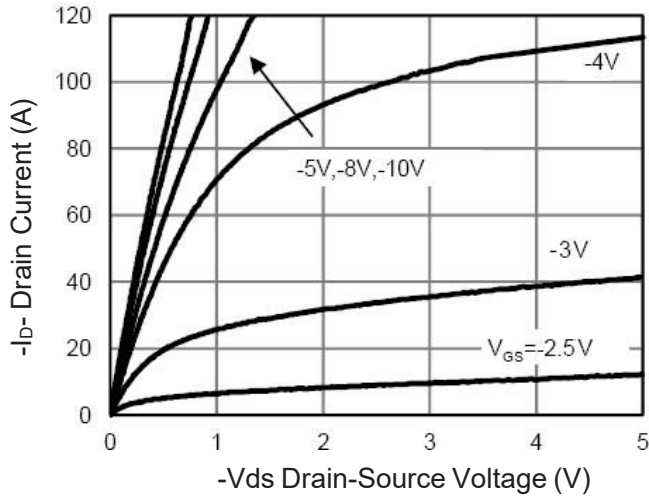


Figure 1 Output Characteristics

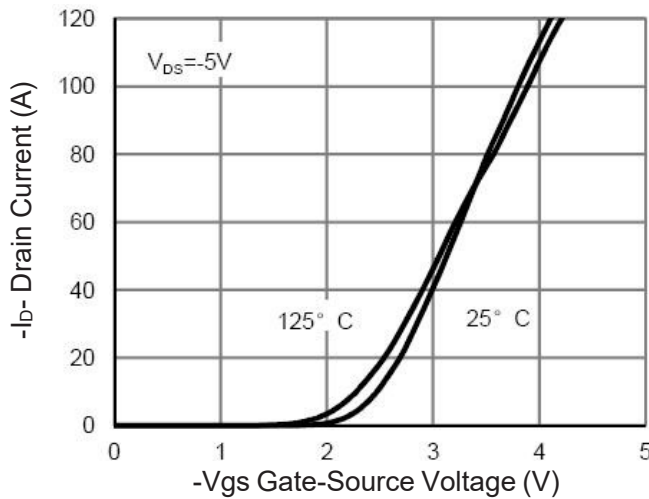


Figure 2 Transfer Characteristics

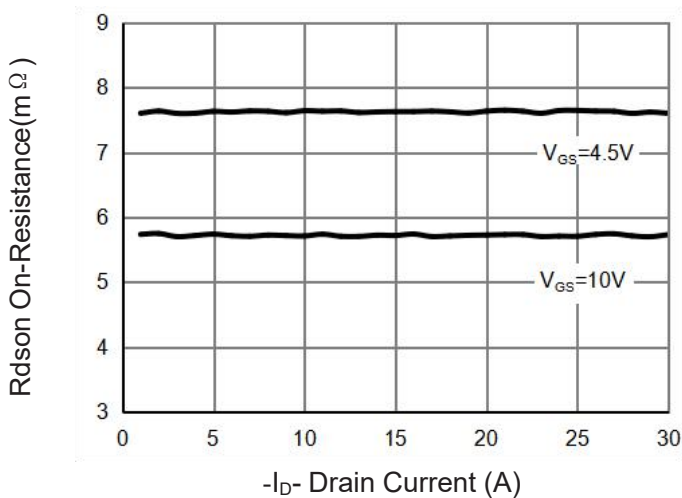


Figure 3 Rdson- Drain Current

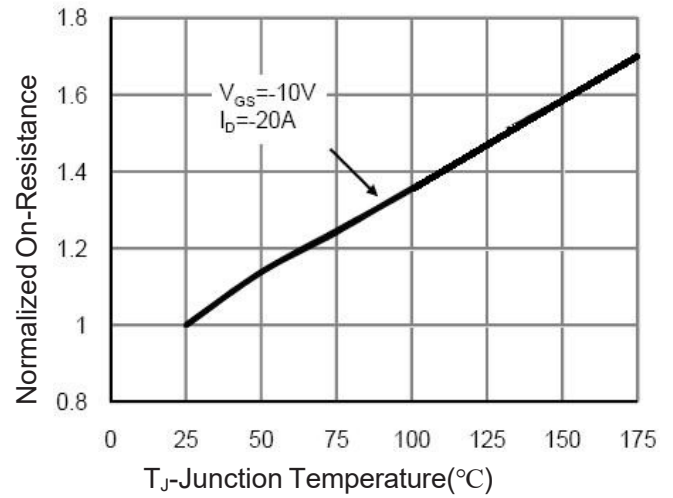


Figure 4 Rdson-Junction Temperature

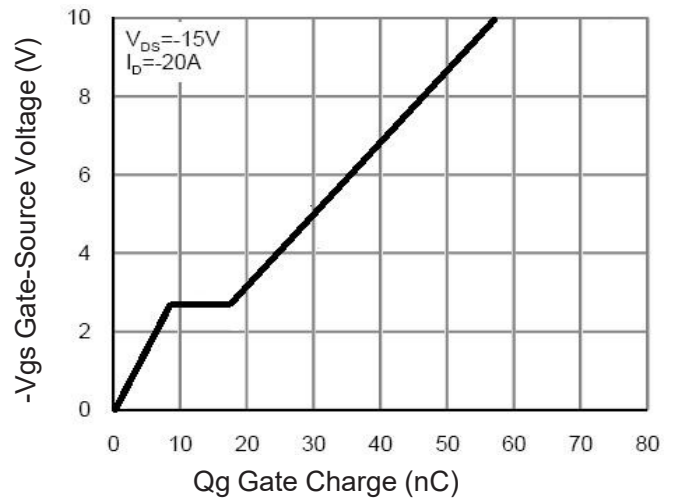


Figure 5 Gate Charge

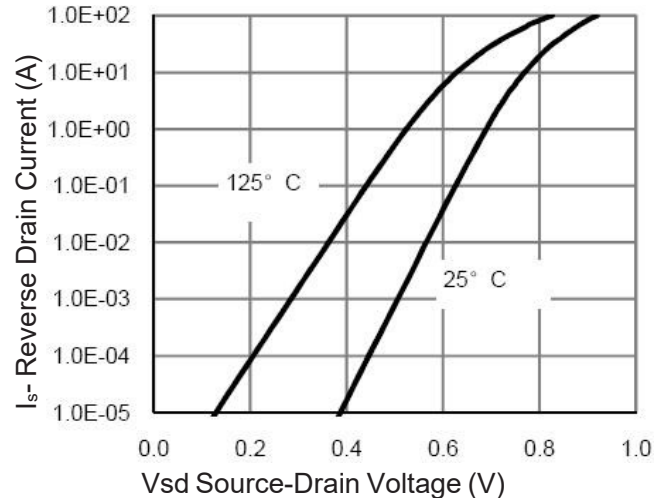
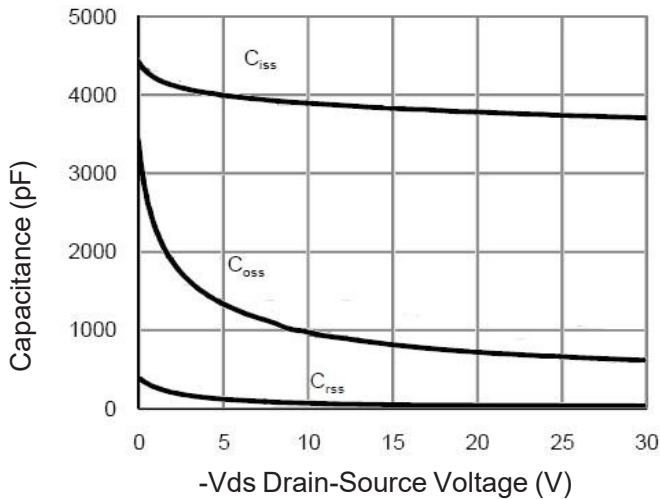
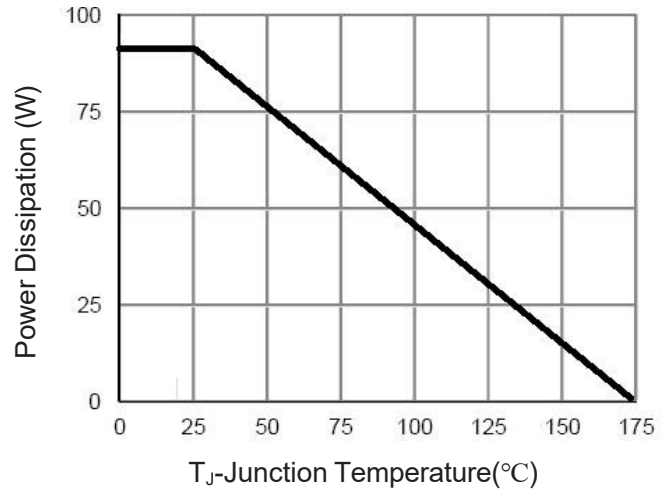
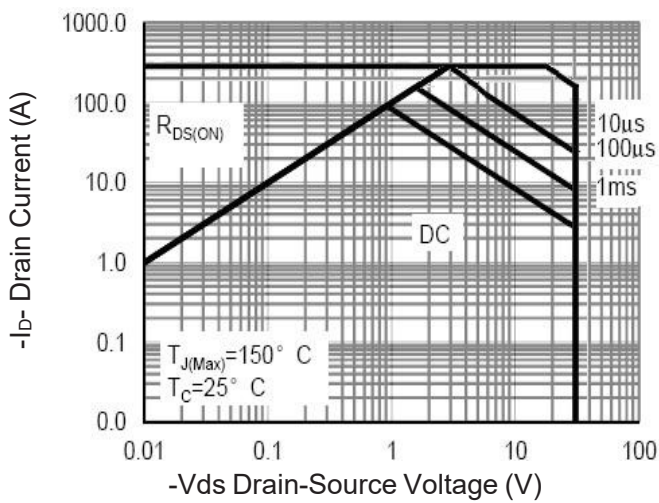
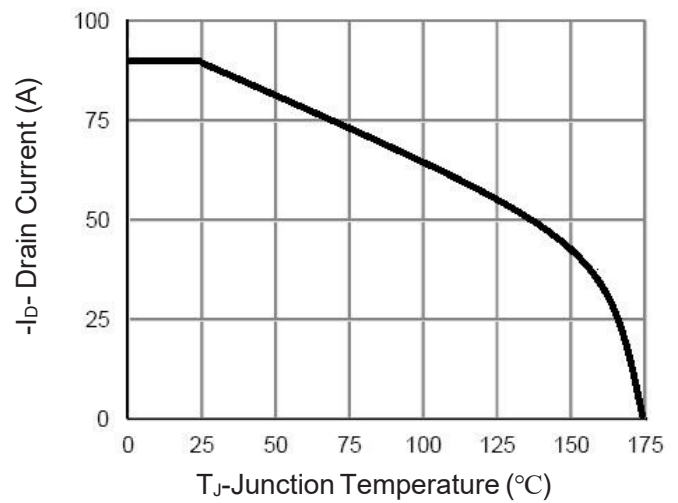
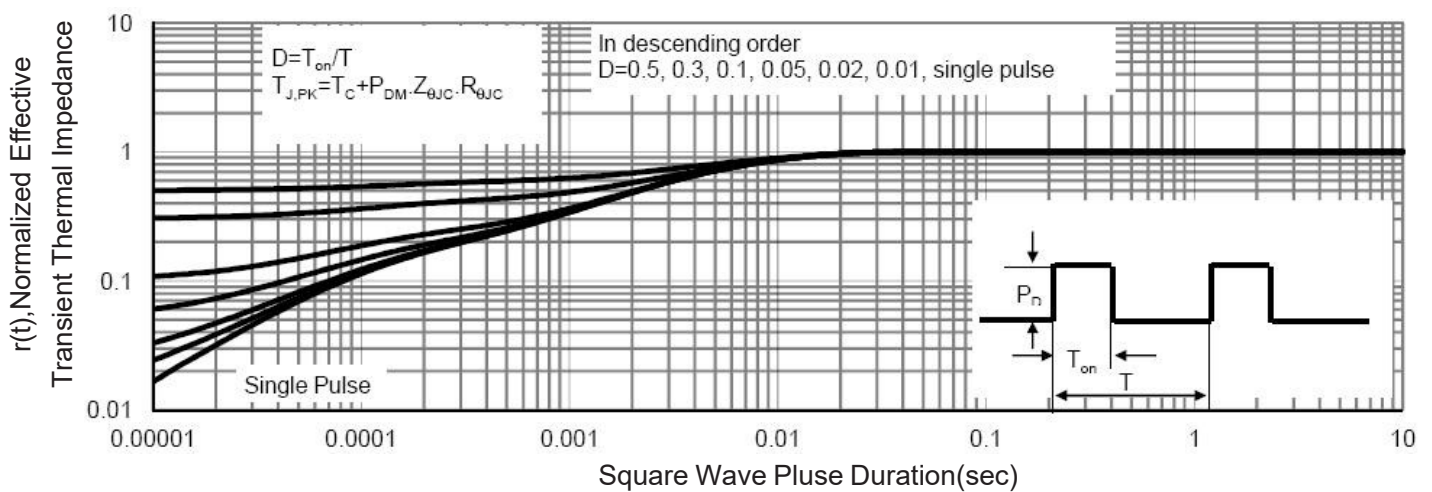


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area

Figure 10 Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance